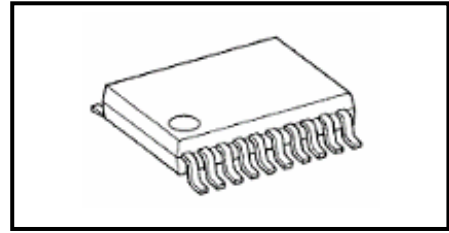


Toshiba Bi-CD Integrated Circuit Silicon Monolithic

# T B 6 5 9 3 F N G

## Driver IC for DC motor

TB6593FNG is a driver IC for DC motor with output transistor in LD MOS structure with low ON-resistor. Two input signals, IN1 and IN2, can choose one of four modes such as CW, CCW, short brake, and stop mode.



## Features

- Power supply voltage :  $V_M=15V$  ( Max. )
- Output current :  $I_{out}=1.2A(ave) / 3.2A$  (peak)
- Output low ON resistor :  $0.35\Omega$  ((typ. @ $V_M=5V$ )
- Standby (Power save)system
- CW/CCW/short brake/stop function modes
- Built-in thermal shutdown circuit and low voltage detecting circuit
- Small faced package ( SSOP20:0.65mm pitch )
- Response to Pb free packaging

Weight

SSOP20-P-225-0.65: 0.09g (Typ.)

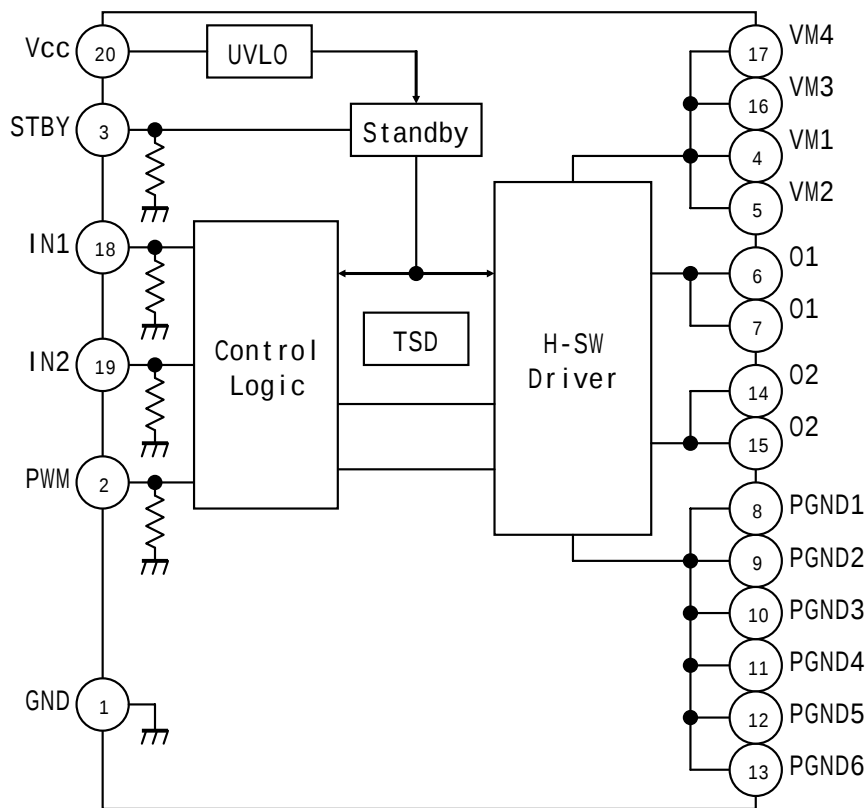
The following conditions apply to solderability:

\*Solderability

1. Use of Sn-37Pb solder bath
  - \*solder bath temperature =  $230^{\circ}C$
  - \*dipping time = 5 seconds
  - \*number of times = once
  - \*use of R-type flux
2. Use of Sn-3.0Ag-0.5Cu solder bath
  - \*solder bath temperature =  $245^{\circ}C$
  - \*dipping time = 5 seconds
  - \*the number of times = once
  - \*use of R-type flux

\* This product has a MOS structure and is sensitive to electrostatic discharge. When handling this product, ensure that the environment is protected against electrostatic discharge by using an earth strap, a conductive mat and an ionizer. Ensure also that the ambient temperature and relative humidity are maintained at reasonable levels.

**Block Diagram**



**Pin Functions**

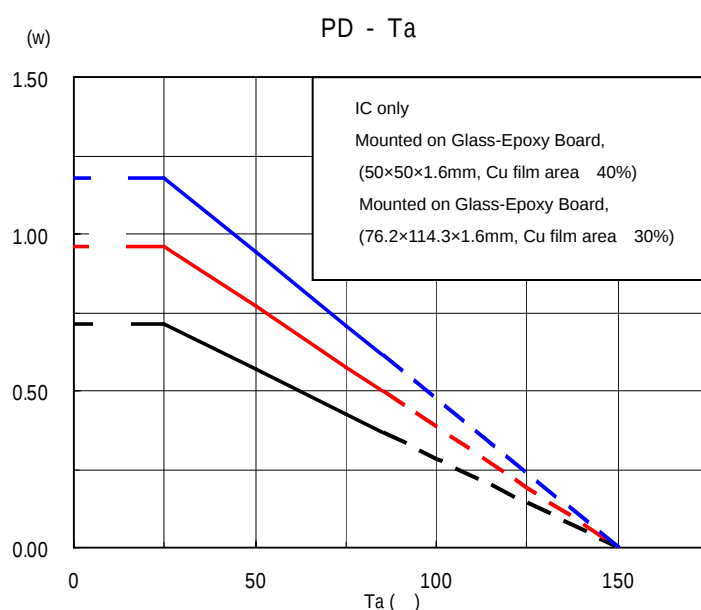
| Pin NO. | Symbol | Characteristics       | Remarks                                           |
|---------|--------|-----------------------|---------------------------------------------------|
| 1       | GND    | Small signal GND      |                                                   |
| 2       | PWM    | PWM signal input      | “H”=Active / 200k $\Omega$ pull-down at internal  |
| 3       | STBY   | Standby signal input  | “L”=standby / 200k $\Omega$ pull-down at internal |
| 4       | VM1    | VM supply             | VM=2.5V~13.5V                                     |
| 5       | VM2    |                       |                                                   |
| 6       | O1     | Output1               |                                                   |
| 7       | O1     |                       |                                                   |
| 8       | PGND1  | Power GND             |                                                   |
| 9       | PGND2  |                       |                                                   |
| 10      | PGND3  |                       |                                                   |
| 11      | PGND4  |                       |                                                   |
| 12      | PGND5  |                       |                                                   |
| 13      | PGND6  |                       |                                                   |
| 14      | O2     | Output2               |                                                   |
| 15      | O2     |                       |                                                   |
| 16      | VM3    | VM supply             | VM=2.5V~13.5V                                     |
| 17      | VM4    |                       |                                                   |
| 18      | IN1    | Control signal nput1  | 200k $\Omega$ pull-down at internal               |
| 19      | IN2    | Control signal input2 |                                                   |
| 20      | Vcc    | Small signal supply   | Vcc=2.7V ~ 5.5V                                   |

## Absolute Maximum Ratings (Ta = 25°C)

| Characteristics       | Symbol      | Rating    | Unit | Remarks                                                                        |
|-----------------------|-------------|-----------|------|--------------------------------------------------------------------------------|
| Supply voltage        | VM          | 15        | V    |                                                                                |
|                       | Vcc         | 6         |      |                                                                                |
| Input voltage         | VIN         | -0.2 ~ 6  | V    | IN1,IN2,STBY,PWM pins                                                          |
| Output voltage        | Vout        | 15        | V    | O1,O2 pins                                                                     |
| Output current        | Iout        | 1.2       | A    |                                                                                |
|                       | Iout (peak) | 3.2       |      | tw=10ms, Superimposed pulse, Duty is 30% or less.                              |
| Power dissipation     | PD          | 1.18      | W    | 76.2×114.3×1.6mm When it is packaged to the board made of glass-epoxy (Cu30%). |
|                       |             | 0.96      |      | 50×50×1.6mm When it is packaged to the board made of glass-epoxy (Cu40%).      |
|                       |             | 0.71      |      | IC only                                                                        |
| Operating temperature | Topr        | -20 ~ 85  |      |                                                                                |
| Storage temperature   | Tstg        | -55 ~ 150 |      |                                                                                |

## Operating Range (Ta = -20 to 85°C)

| Characteristics       | Symbol | Min | Typ. | Max  | Unit |
|-----------------------|--------|-----|------|------|------|
| Supply voltage        | Vcc    | 2.7 | 3    | 5.5  | V    |
|                       | VM     | 2.5 | 5    | 13.5 | V    |
| Output current (H-SW) | Iout   | --- | ---  | 1.0  | A    |
| Switching frequency   | fPWM   | --- | ---  | 100  | kHz  |

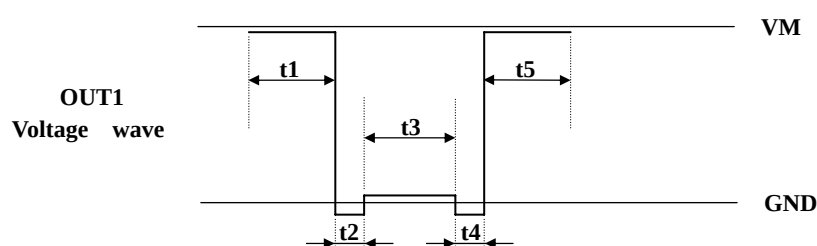
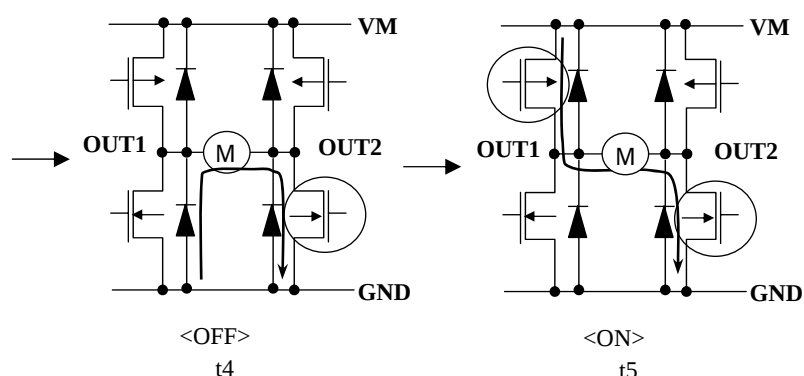
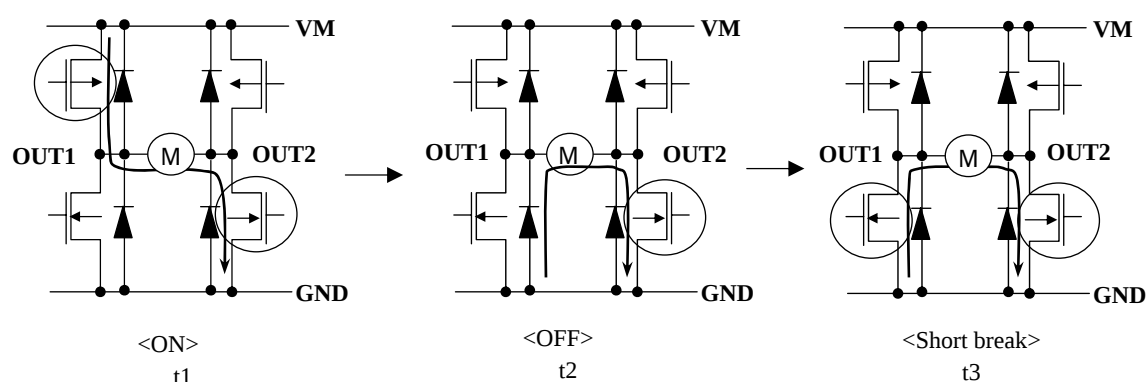


## H-SW Control Function

| Input |       |     |      | Output                  |      |             |
|-------|-------|-----|------|-------------------------|------|-------------|
| IN1   | IN2   | PWM | STBY | OUT1                    | OUT2 | Mode        |
| H     | H     | H   | H    | L                       | L    | Short brake |
| L     | H     | H   | H    | L                       | H    | CCW         |
|       |       | L   | H    | L                       | L    | Short brake |
| H     | L     | H   | H    | H                       | L    | CW          |
|       |       | L   | H    | L                       | L    | Short brake |
| L     | L     | H   | H    | OFF<br>(High impedance) |      | Stop        |
| H / L | H / L | H   | L    | OFF<br>(High impedance) |      | Standby     |

## H-SW Operating Description

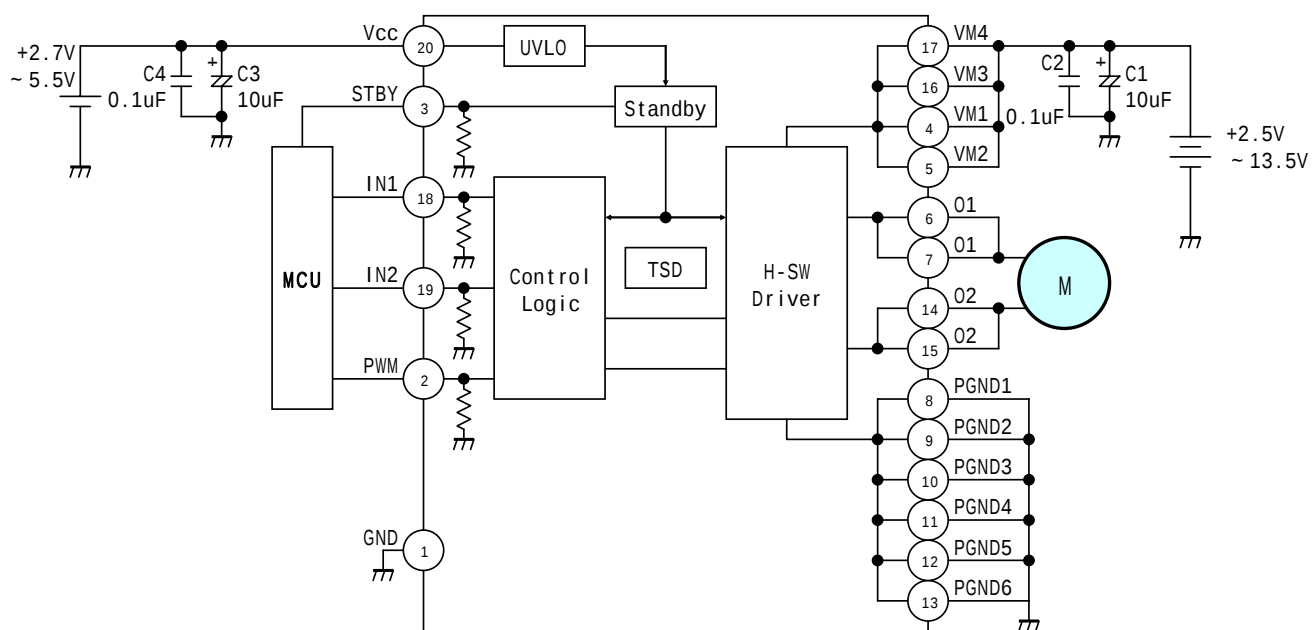
•To prevent penetrating current, dead time  $t_2$  and  $t_4$  (300ns : Designed value )is provided in switching to each mode in the IC.



**Electrical Characteristics (unless otherwise specified,  $V_{CC} = 3\text{ V}$ ,  $V_M = 4.5\text{ V}$ ,  $T_a = 25^\circ\text{C}$ )**

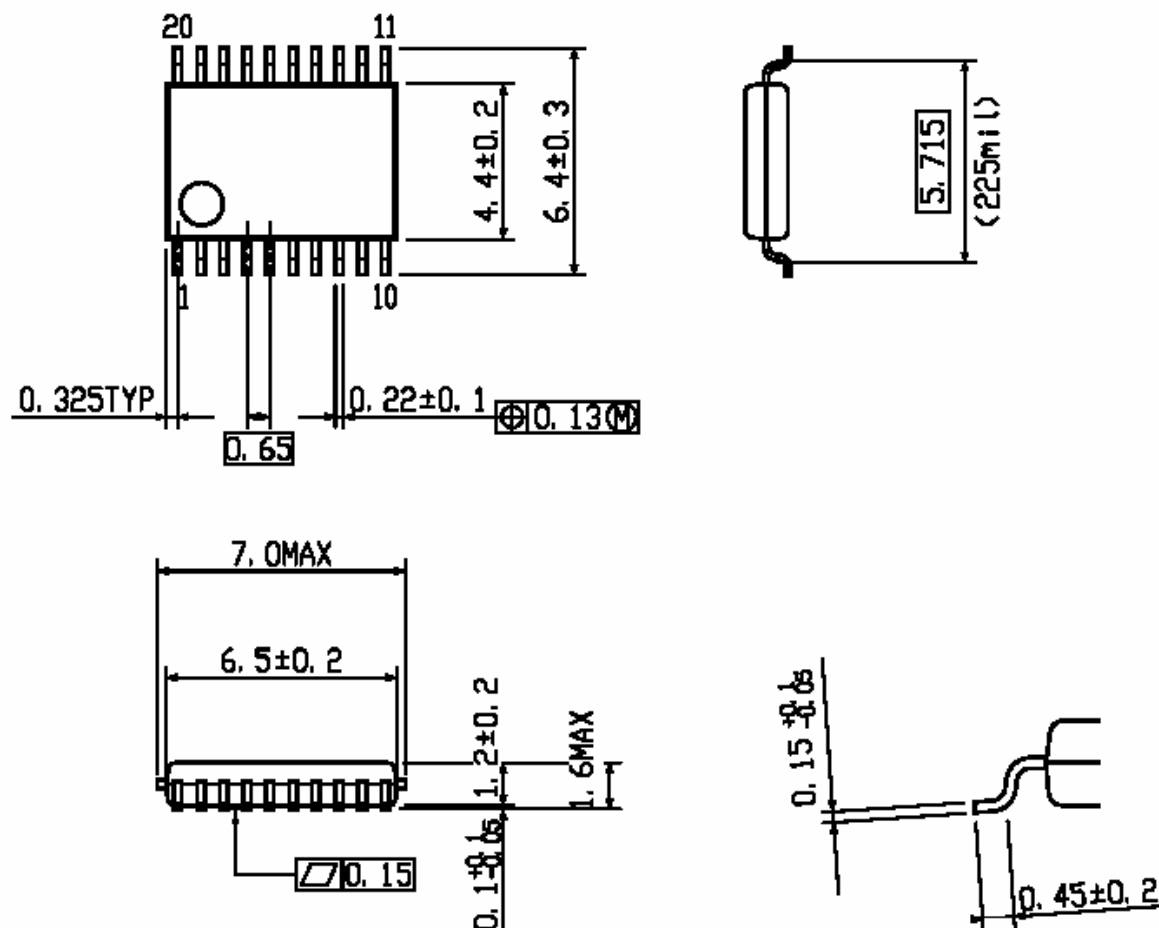
| Characteristics                                | Symbol               | Test Condition                        | Min  | Typ. | Max          | Unit          |
|------------------------------------------------|----------------------|---------------------------------------|------|------|--------------|---------------|
| Supply current                                 | $I_{cc}$             | STBY= $V_{CC}$                        | ---  | 0.9  | 1.2          | mA            |
|                                                | $I_{cc}(\text{STB})$ | STBY=0V                               | ---  | ---  | 1            | $\mu\text{A}$ |
|                                                | $I_M(\text{STB})$    |                                       | ---  | ---  | 1            |               |
| Control input voltage                          | $V_{IH}$             |                                       | 2    | ---  | $V_{CC}+0.2$ | V             |
|                                                | $V_{IL}$             |                                       | -0.2 | ---  | 0.8          |               |
| Control input current                          | $I_{IH}$             | $V_{IN}=3\text{ V}$                   | 5    | 15   | 25           | $\mu\text{A}$ |
|                                                | $I_{IL}$             | $V_{IN}=0\text{ V}$                   | ---  | ---  | 1            |               |
| Standby input voltage                          | $V_{IH}(\text{STB})$ |                                       | 2    | ---  | $V_{CC}+0.2$ | V             |
|                                                | $V_{IL}(\text{STB})$ |                                       | -0.2 | ---  | 0.8          |               |
| Standby input current                          | $I_{IH}(\text{STB})$ | $V_{IN}=3\text{ V}$                   | 5    | 15   | 25           | $\mu\text{A}$ |
|                                                | $I_{IL}(\text{STB})$ | $V_{IN}=0\text{ V}$                   | ---  | ---  | 1            |               |
| Output saturating voltage                      | $V_{sat}(U+L)$       | $I_o=1\text{ A}$                      | ---  | 0.35 | 0.5          | V             |
| Output leakage current                         | $I_L(U)$             | $V_M=V_{out}=15\text{ V}$             | ---  | ---  | 1            | $\mu\text{A}$ |
|                                                | $I_L(L)$             | $V_M=15\text{ V}, V_{out}=0\text{ V}$ | -1   | ---  | ---          |               |
| Regenerative diode $V_F$                       | $V_F(U)$             | $I_F=1\text{ A}$                      | ---  | 1    | 1.1          | V             |
|                                                | $V_F(L)$             |                                       | ---  | 1    | 1.1          |               |
| Low voltage detecting voltage                  | UVLD                 | ( Designed value )                    | ---  | 2.0  | ---          | V             |
| Recovering voltage                             | UVLC                 |                                       | ---  | 2.2  | ---          |               |
| Thermal shutdown circuit operating temperature | TSD                  | ( Designed value )                    | ---  | 170  | ---          |               |
| Thermal shutdown hysteresis                    | $\Delta\text{TSD}$   |                                       | ---  | 20   | ---          |               |

## Typical Application Diagram



Note : The power supply capacitor should be connected as close as possible to the IC.

Unit: mm



Weight: 0.09 g (Typ.)

**Notes on Contents****1. Block Diagrams**

Some of the functional blocks, circuits, or constants in the block diagram may be omitted or simplified for explanatory purposes.

**2. Equivalent Circuits**

The equivalent circuit diagrams may be simplified or some parts of them may be omitted for explanatory purposes.

**3. Timing Charts**

Timing charts may be simplified for explanatory purposes.

**4. Application Circuits**

The application circuits shown in this document are provided for reference purposes only. Thorough evaluation is required, especially at the mass production design stage.

Toshiba does not grant any license to any industrial property rights by providing these examples of application circuits.

**5. Test Circuits**

Components in the test circuits are used only to obtain and confirm the device characteristics. These components and circuits are not guaranteed to prevent malfunction or failure from occurring in the application equipment.

**IC Usage Considerations****Notes on handling of ICs**

- [1] The absolute maximum ratings of a semiconductor device are a set of ratings that must not be exceeded, even for a moment. Do not exceed any of these ratings.  
Exceeding the rating(s) may cause the device breakdown, damage or deterioration, and may result injury by explosion or combustion.
- [2] Use an appropriate power supply fuse to ensure that a large current does not continuously flow in case of over current and/or IC failure. The IC will fully break down when used under conditions that exceed its absolute maximum ratings, when the wiring is routed improperly or when an abnormal pulse noise occurs from the wiring or load, causing a large current to continuously flow and the breakdown can lead smoke or ignition. To minimize the effects of the flow of a large current in case of breakdown, appropriate settings, such as fuse capacity, fusing time and insertion circuit location, are required.
- [3] If your design includes an inductive load such as a motor coil, incorporate a protection circuit into the design to prevent device malfunction or breakdown caused by the current resulting from the inrush current at power ON or the negative current resulting from the back electromotive force at power OFF. IC breakdown may cause injury, smoke or ignition.  
Use a stable power supply with ICs with built-in protection functions. If the power supply is unstable, the protection function may not operate, causing IC breakdown. IC breakdown may cause injury, smoke or ignition.
- [4] Do not insert devices in the wrong orientation or incorrectly.  
Make sure that the positive and negative terminals of power supplies are connected properly.  
Otherwise, the current or power consumption may exceed the absolute maximum rating, and exceeding the rating(s) may cause the device breakdown, damage or deterioration, and may result injury by explosion or combustion.  
In addition, do not use any device that is applied the current with inserting in the wrong orientation or incorrectly even just one time.

**Points to remember on handling of ICs****(1) Thermal Shutdown Circuit**

Thermal shutdown circuits do not necessarily protect ICs under all circumstances. If the thermal shutdown circuits operate against the over temperature, clear the heat generation status immediately.

Depending on the method of use and usage conditions, such as exceeding absolute maximum ratings can cause the thermal shutdown circuit to not operate properly or IC breakdown before operation.

**(2) Heat Radiation Design**

In using an IC with large current flow such as power amp, regulator or driver, please design the device so that heat is appropriately radiated, not to exceed the specified junction temperature ( $T_J$ ) at any time and condition. These ICs generate heat even during normal use. An inadequate IC heat radiation design can lead to decrease in IC life, deterioration of IC characteristics or IC breakdown. In addition, please design the device taking into consideration the effect of IC heat radiation with peripheral components.

**(3) Back-EMF**

When a motor rotates in the reverse direction, stops or slows down abruptly, a current flows back to the motor's power supply due to the effect of back-EMF. If the current sink capability of the power supply is small, the device's motor power supply and output pins might be exposed to conditions beyond maximum ratings. To avoid this problem, take the effect of back-EMF into consideration in system design.

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